MOSFETs Silicon Carbide N-Channel MOS

TW015N65C

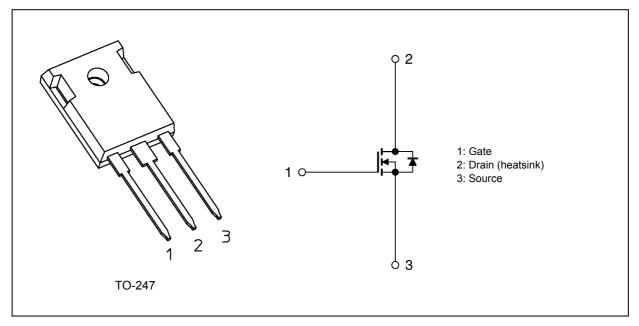
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: V_{DSF} = -1.35 V (typ.)
- (3) High voltage: $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 15 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 11.7 mA)
- (6) Enhancement mode.

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

	Characteristics	Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	650	V
Gate-source voltage		V _{GSS}	+25/-10	
Drain current (DC)	(T _c = 25 °C)	I _D	100	A
Drain current (DC)	(T _c = 100°C)	I _D	82	
Drain current (pulsed)	(T _c = 25 °C)	I _{DP}	360	
Drain current (pulsed)	(T _c = 100°C)	I _{DP}	270	
Power dissipation	(T _c = 25°C)	PD	342	W
Channel temperature		T _{ch}	175	°C
Storage temperature		T _{stg}	-55 to 175	
Mounting torque		TOR	0.8	N·m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.438	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.

6. Electrical Characteristics

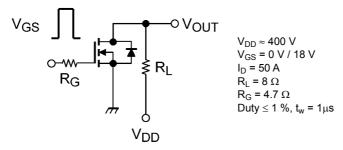
6.1. Static Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = +25/-10 V, V _{DS} = 0 V		—	±0.1	μA
Drain cut-off current		I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V		14	100	
			T _a = 150 °C, V _{DS} = 650 V, V _{GS} = 0 V	—	72	_	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 4 mA, V _{GS} = 0 V	650		_	V
Gate threshold voltage (N	Note 2)	V _{th}	V _{DS} = 10 V, I _D = 11.7 mA	3.0	_	5.0	
Drain-source on-resistance		R _{DS(ON)}	V _{GS} = 18 V, I _D = 50 A	—	15	21	mΩ
			T _a = 150 °C, V _{GS} = 18 V, I _D = 50 A	_	16		

Note 2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 400 V, V _{GS} = 0 V,		4850	—	pF
Reverse transfer capacitance	C _{rss}	f = 100 kHz	_	12	—	
Output capacitance	C _{oss}		_	500	_	
Output charge	Q _{oss}			337	—	nC
C _{oss} stored energy	E _{oss}		_	46	—	μJ
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz		1.0	_	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	79	—	ns
Switching time (turn-on time)	t _{on}		_	117	—	
Switching time (fall time)	t _f]		59	_	
Switching time (turn-off time)	t _{off}		_	116	_	





6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		$V_{DD} \approx 400$ V, V_{GS} = 18 V, I_D = 50 A	—	128	—	nC
Gate-source charge 1	Q _{gs1}		_	50	_	
Gate-drain charge	Q _{gd}		_	19	_	

6.4. Source \cdot Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 3)	I _{DR}	T _c = 25 °C, V _{GS} = -5 V	_	_	100	A
			T _c = 100 °C, V _{GS} = -5 V	—	_	73	
			T _c = 25 °C, V _{GS} = 18 V	_	_	100	
			T _c = 100 °C, V _{GS} = 18 V	_	_	82	
Reverse drain current	(Note 3)	I _{DRP}	T _c = 25 °C, V _{GS} = -5 V	_	_	360	
(pulsed)			T _c = 100 °C, V _{GS} = -5 V	_	_	146	
			T _c = 25 °C, V _{GS} = 18 V	_	_	360	
			T _c = 100 °C, V _{GS} = 18 V	_	_	270	
Diode forward voltage		V _{DSF}	I _{DR} = 45 A, V _{GS} = -5 V	_	-1.35	-1.80	V
			T _a = 150 °C, I _{DR} = 45 A, V _{GS} = -5 V	—	-1.64	_	
Reverse recovery time		t _{rr}	I _{DR} = 33 A, V _{GS} = 0 V,	_	60	—	ns
Reverse recovery charge		Q _{rr}	V _{DD} = 400 V, -dI _{DR} /dt = 1000 A/μs	_	510		nC
Peak reverse recovery current		I _{rr}		—	17	_	A

Note 3: Ensure that the channel temperature does not exceed 175 °C.

7. Marking (Note)

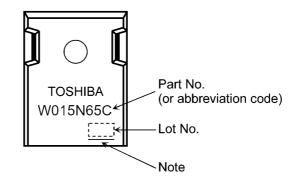
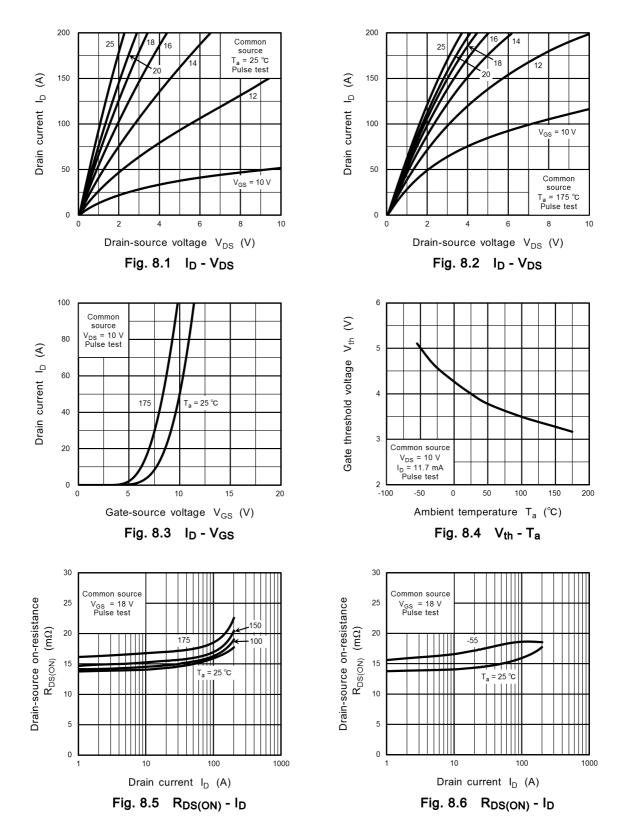
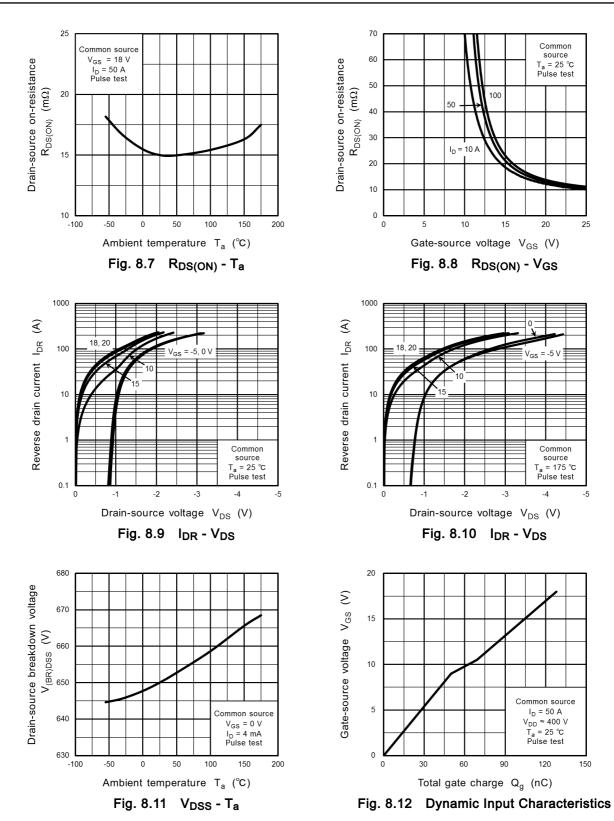


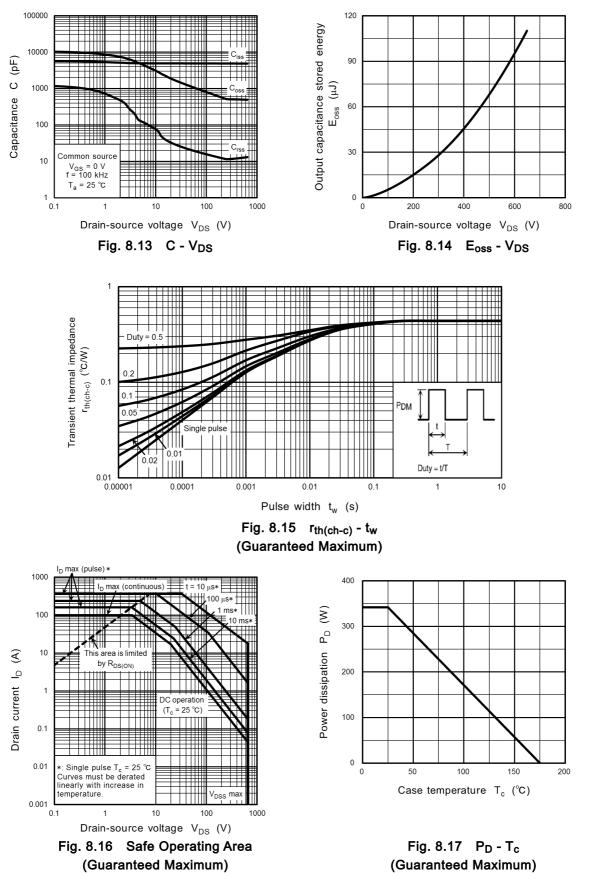
Fig. 7.1 Marking

 Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
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8. Characteristics Curves (Note)





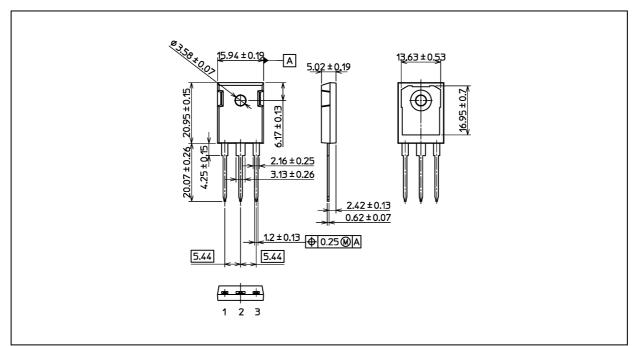


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TW015N65C

Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

	Package Name(s)
TOSHIBA: 2-16L1A	
Nickname: TO-247	

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